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Why separate report for 600mV output:

[PMP9738](#) has same physical design and was tested at 1.0 Vout. However, going down to 600mV with 12Vin changes the control mode of the TPS53661 from a quasi fixed frequency control with active current sharing to a fixed on time control per phase with no active current sharing. This is because of minimum pulse width of about 260 nsec per phase for the 300 kHz setting. The customer asked, “What will happen without active current sharing when power stages with normal variations in Rdson - on resistance are used?”

Also, actual switching frequency gets reduced as Vout is reduced, and ripple / dynamic response can be affected. This report first shows dynamic response & ripple for the 600mV setting. Then thermal images for two models with 5 phases each and 600mV at 200 A are shown, followed by 1.0 Vout at 200 A for comparison; and then detailed efficiency / loss data on one of the models at 600 mV out.

Finally, an experiment with (see pages 10-14) “worst case” FET on resistance variation is shown. Here, 3 phases are used and the middle phase power stage is replaced with higher on resistance / lower current rated CSD95373B. Load is set at 120 A or 40 A per phase off the 600mV output, and Vin is varied from 7 V when mode is still fixed frequency up 12V. Between 8 and 9 Vin, mode transitions to fixed pulse width and frequency starts to drop from 318 kHz reaching 226 kHz at 12 Vin. Thermal images show that heat sharing is actually improved by going to the fixed pulse width mode. Also, the combined lower frequency and improved thermal sharing create an increased efficiency with increased Vin, which is unusual for buck converters.

Summary / comments on dynamic load testing:

Tested on Model t11: Loop compensation values: C46=10pF; C47=1.5nF; R68=19.1k
Comments: Waveforms shown with a static load of 106 A off the output. However, same tests were also done with no static load, and very similar undershoots & overshoots seen. This is because of the Forced Continuous conduction Mode (FCCM) operation.

Step load was 70 A in about 8 usec and load dump was 85 A in 5 usec. Hence, load dump overshoot of 42 mV is higher than step load undershoot of 30 mV.

The on board dynamic load allows speeds of step load and load dump to be adjusted independently based on actual needs of the application.

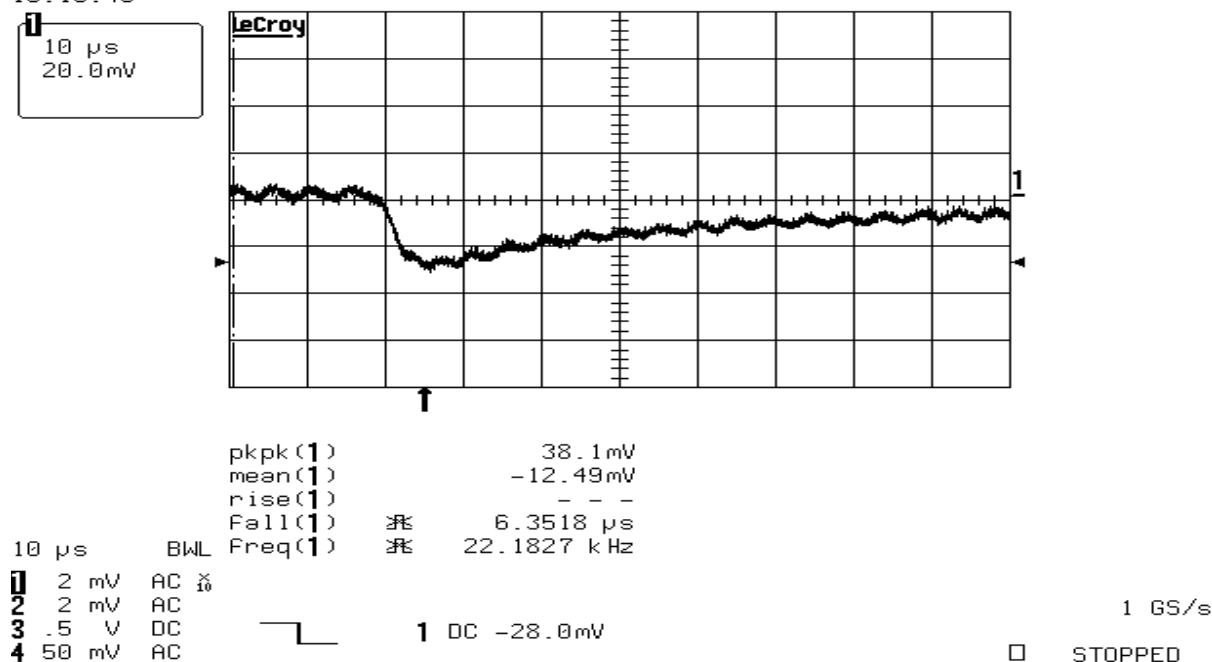
The 106A static load is an external load bank, the dynamic load is on the board. See page 3 of the schematic.

600 mV 300kHz settings: actual frequency at 600 mV off 12.0 Vin about 200 kHz

Vout measured at C19: All 6 phases on

Step load response from 106 A to 176 A (70 A step) in 8 usec: ~30 mV

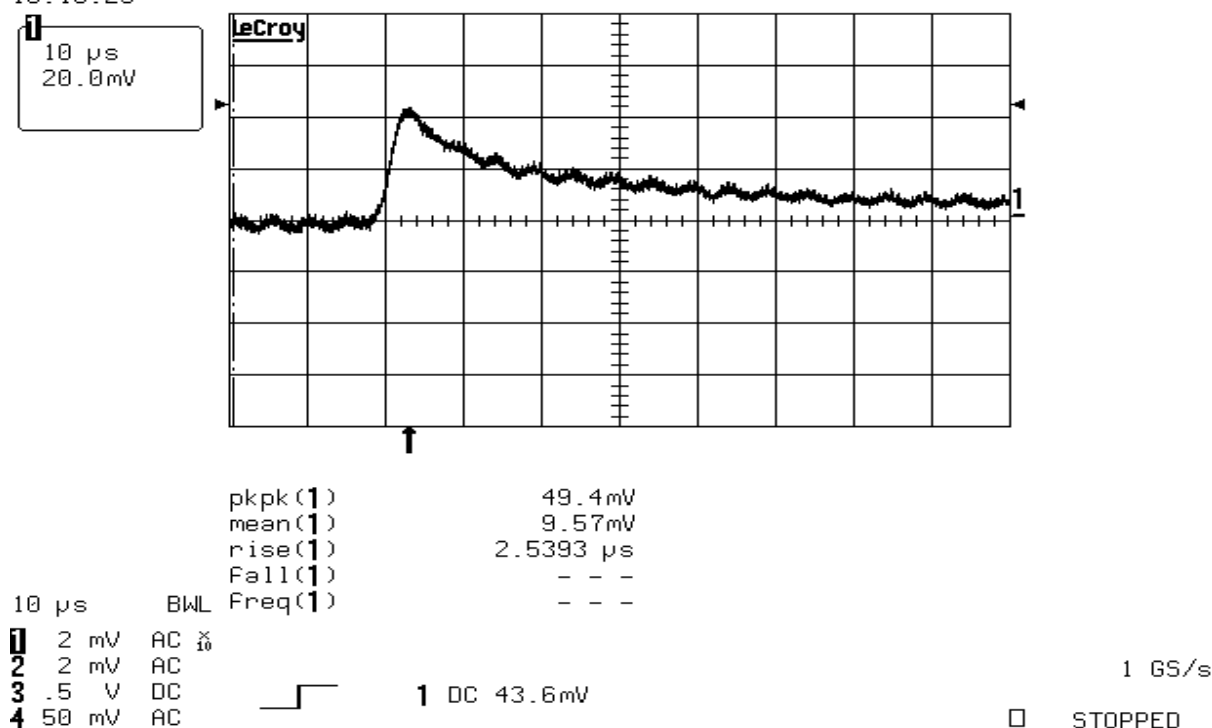
29-Dec-14
18:16:43



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Load dump response from 191 A to 106 A (85 A step) in 5 usec: ~42 mV

29-Dec-14
18:18:25

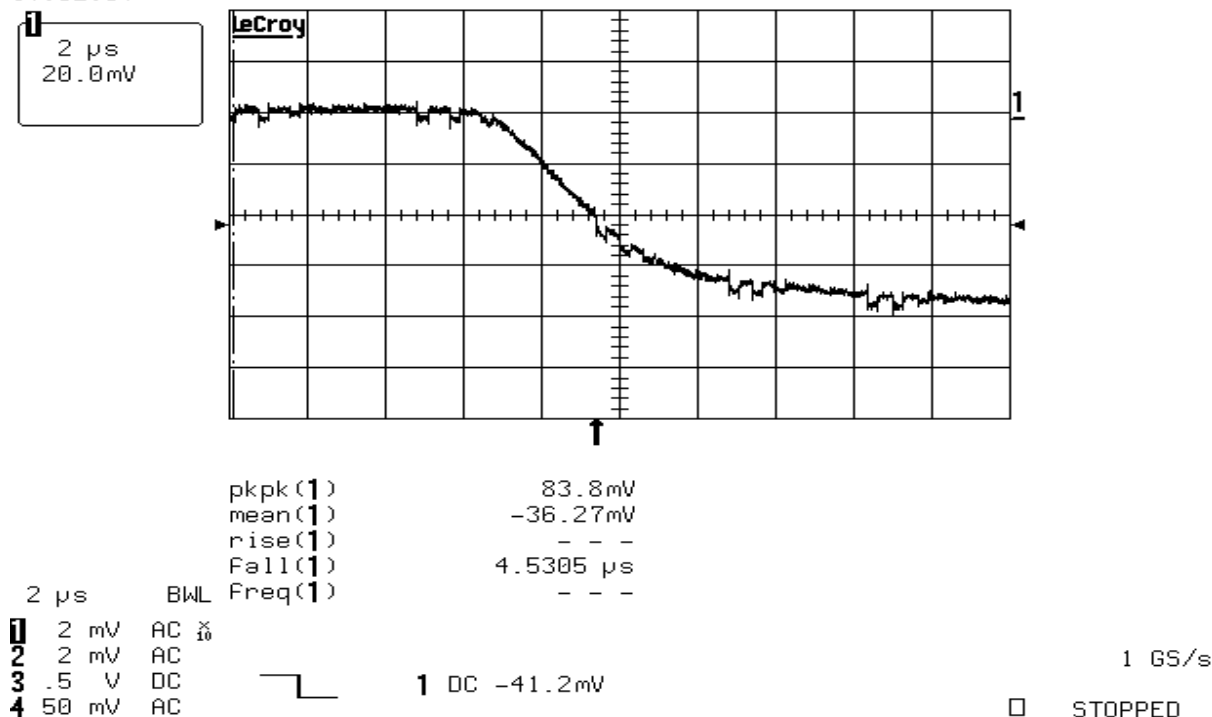


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Waveforms across resistors in dynamic load bank used to calculate step load current and speed: There are two resistor paths from Vout; R1 and R2 each 2mOhm and tied to Vout. Hence, the total load step is the sum of both. Here scope ground on Vout side of resistor.

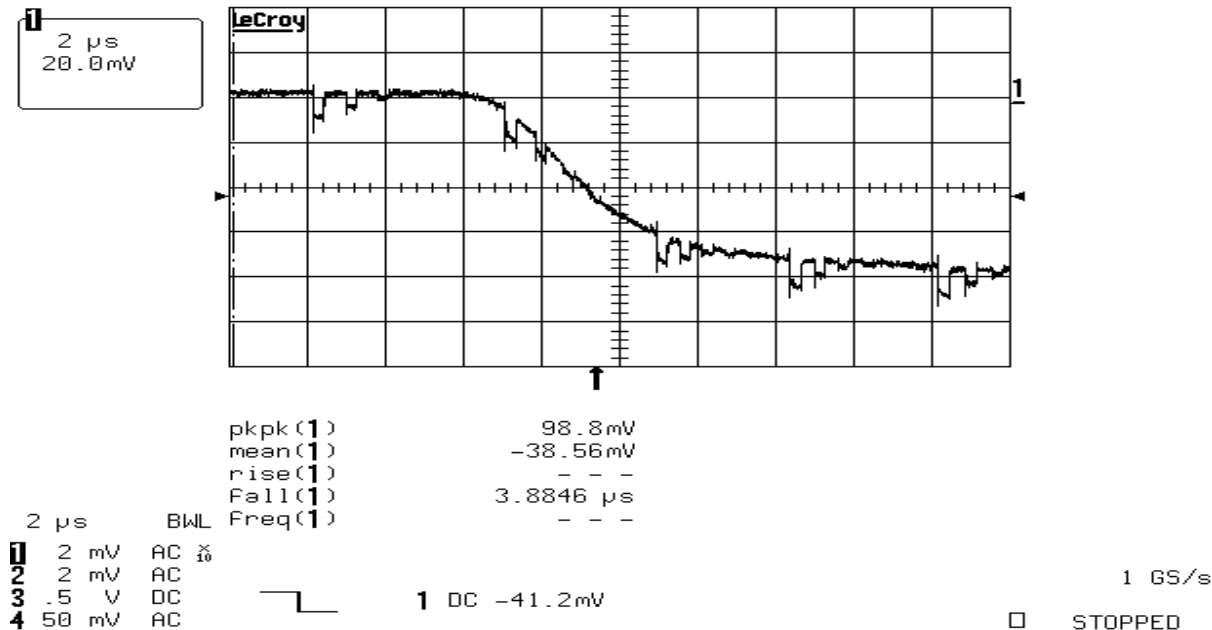
First R1 2mOhm: 70 mV in 8 usec or 35 A in 8 usec

29-Dec-14
17:32:57



And now R2(also 2mOhm): also 70 mV in 8 usec or 35 A in 8 usec

29-Dec-14
17:33:20

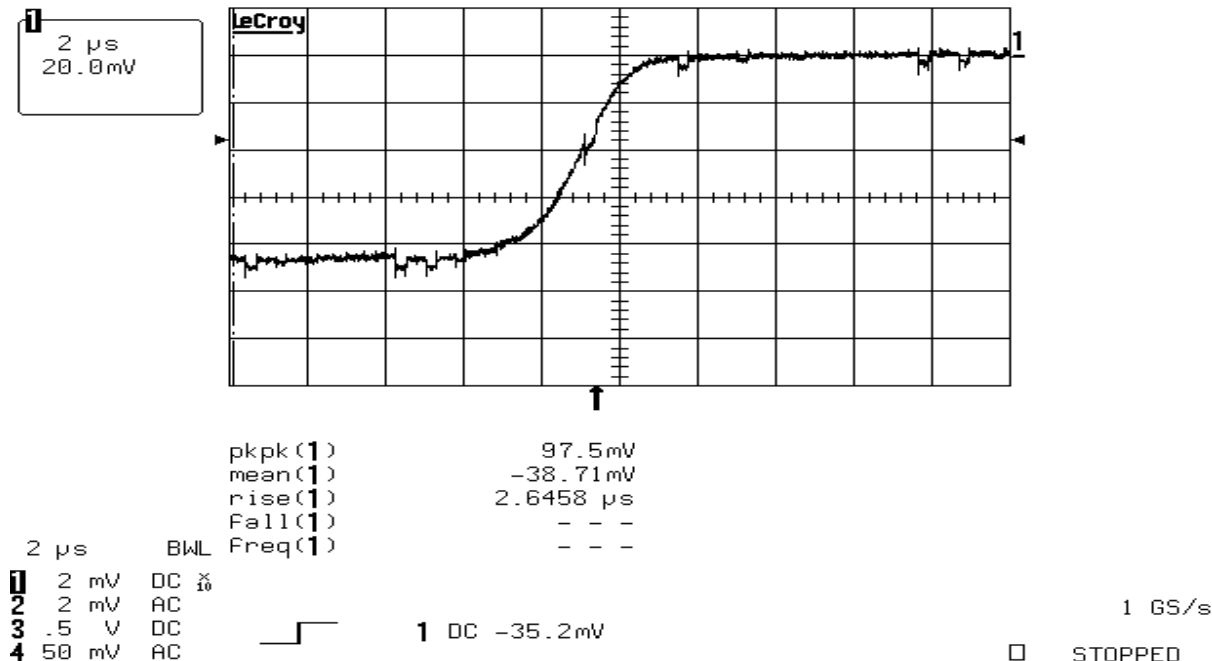


Load strings are in parallel driven by same FET Q1: Hence, combined: 70 A in 8 usec

Waveforms across resistors in dynamic load bank used to calculate load dump current and speed: There are two resistor paths from Vout; R1 and R2 each 2mOhm and tied to Vout. Hence, the total load dump is the sum of both. Here scope ground on Vout side of resistor.

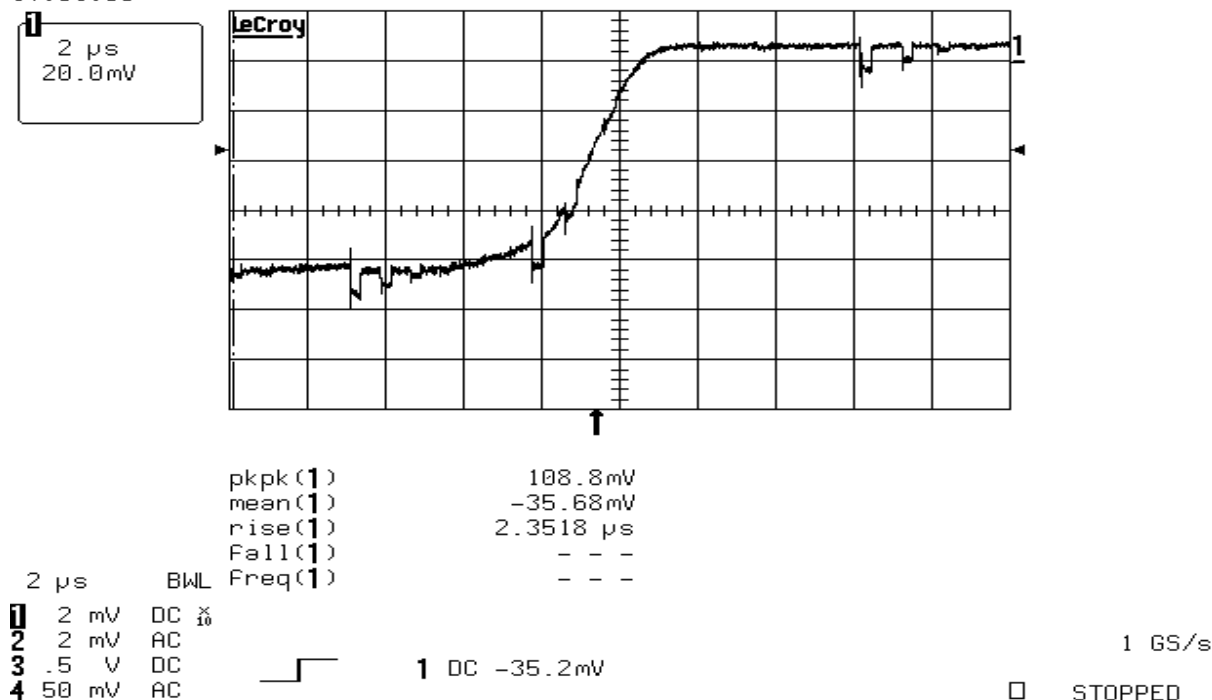
First R1 2mOhm: 84 mV in 5 usec or 42 A in 5 usec

29-Dec-14
17:31:25



And now R2(also 2mOhm): 86 mV in 5 usec or 43 A in 5 usec

29-Dec-14
17:31:05



Load strings are in parallel driven by same FET Q1: Hence, combined: 85 A in 5 usec

Model t12 thermals:

PMP9738 adjusted to 5 phases 600mV 12Vin 220kHz actual

25.0 W on PCB ~300 LFM fan blowing in from U100 side

Ambient 21-23 degrees Celsius

Left to right: U100 thru U500 temperatures in deg. C: 56.7, 60.5, 62.2, 61.2, 56.7

traces / snubbers slightly hotter with hotspot near U300 at 62.6 degrees C

Inductor tops Left to Right (L100 thru L500) in degrees C: 41, 44, 45, 44, 41



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Current senses from the CSD95372Bs: Ref in for all at 1.700 V

Iout (pin 1) for each going from left to right in Volts: 1.886; 1.883, 1.887, 1.891, 1.889

Currents in each based upon 5mV/A sense: 37.2 A; 36.6 A, 37.4 A; 38.2 A, 37.8 A

Here, overall variation 1.6A overall variation or 187.2A in all per senses.

PMP-10393 600 mV 120/200A 5-6 phases off 12Vin Test Report (TPS53661 / CSD95372B)
Texas Instruments

Model t11 thermals: (voltage sense here further away from power train and Voltage at same sense points at 200 A load 12 mV higher at 611.4 mV vs. 599.5 mV on model t12)

PMP9738 adjusted to 5 phases 600mV 12Vin 225kHz actual

25.8 W on PCB ~300 LFM fan blowing in from U100 side

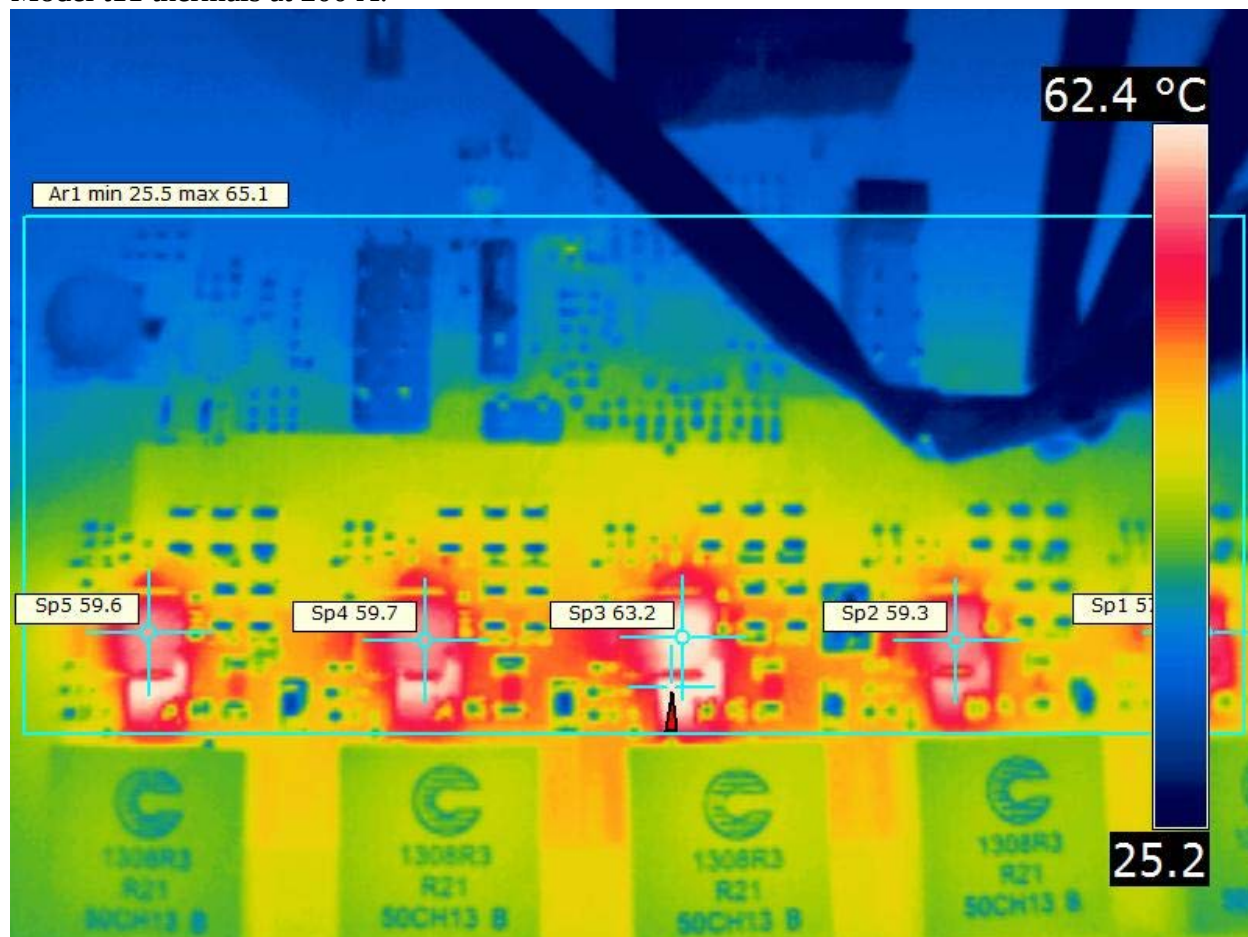
Ambient 21-23 degrees Celsius: (60 deg. C on GUI)

Left to right: U100 thru U500 temperatures in deg. C: 59.6, 59.7, 63.2, 59.3, 57.0

traces / snubbers slightly hotter with hotspot near U300 at 65.1 degrees C

Inductor tops Left to Right (L100 thru L500) in degrees C: 42, 44, 44, 43, 41

Model t11 thermals at 200 A:



11.9992 Vin, 12.371 Ain, 611.4mVout 200.6A out 25.79 W loss

Current senses from the CSD95372Bs: Ref in for all at 1.699 V

Iout (pin 1) for each going from left to right in Volts: 1.908; 1.881; 1.895; 1.881; 1.893

Currents in each based upon 5mV/A sense: 41.8A, 36.4A, 39.2A, 36.4A, 38.8A

Here, overall variation 5.4A overall variation or 192.6A in all per senses.

PMP-10393 600 mV 120/200A 5-6 phases off 12Vin Test Report (TPS53661 / CSD95372B)
Texas Instruments

Model t11 at 1.0Vout 200A off 12 Vin 5 phases:

PMP9738 adjusted to 5 phases 1.0V 12Vin318kHz actual

29.5 W on PCB ~300 LFM fan blowing in from U100 side

LtoR ambient 21-23 deg. C

U100 thru U500 power stages (left to right) max in degrees Celsius: 62, 68, 70, 68, 61

Inductors Left to Right: (L100 thru L500 tops) in degrees Celsius: 43, 47, 47, 46, 44

IR777 at 70 max, 318kHz



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11.999Vin 1.0155Vout, 19.437Ain 200.6Aout or 87.3% eff. Or 29.515W loss on board:

PMP-10393 600 mV 120/200A 5-6 phases off 12Vin Test Report (TPS53661 / CSD95372B) Texas Instruments

Model t12:

Model used for automatic efficiency run: Data is on next page

Model first stabilized at 200 A load off 12 Vin with 300 LFM fan for 20+ minutes. Then load stepped down from 200 A to zero A in 40 steps of 5 A each with 90 seconds between each step

Switching frequencies at various loads:

200 A – 220 kHz; 180 A - 216 kHz; 80 A – 199.5 kHz; 35 A – 192.5 kHz

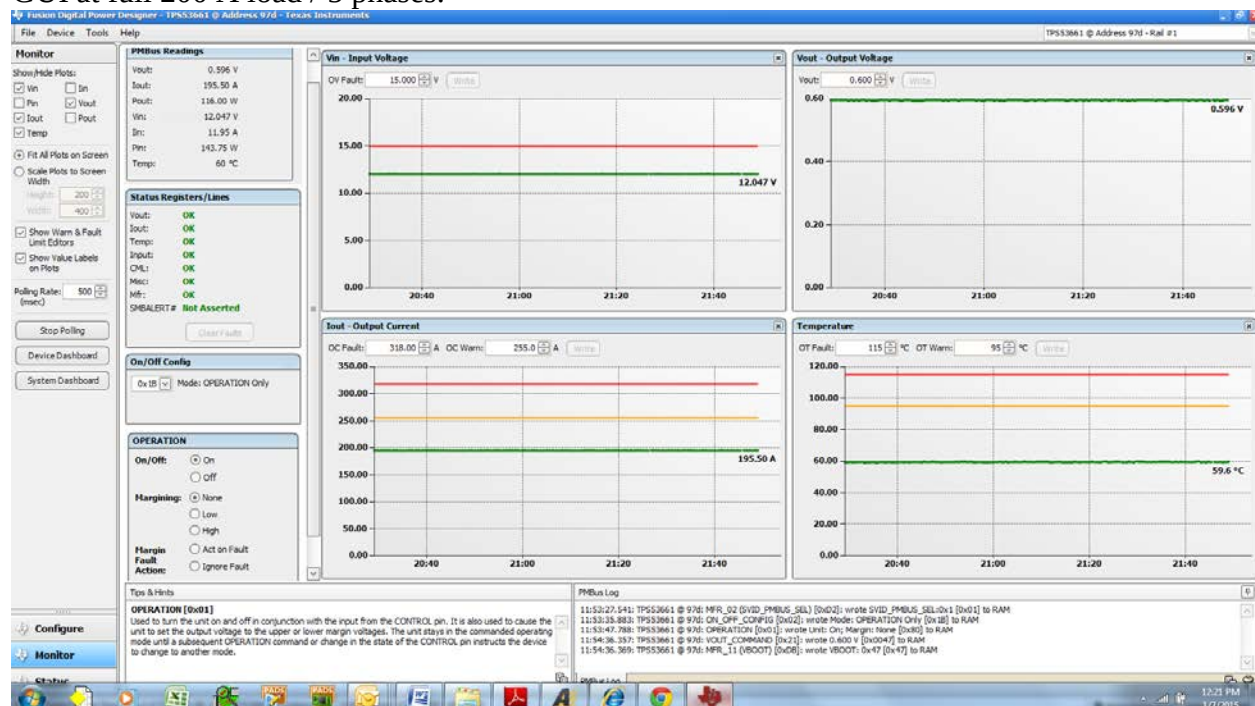
At 200 A load:

Going to 6 stages saves about 3.1W.

Going to 4 stages at 200A increases losses by about 6.2W.

Marginal efficiency near 200 A is just over 71%.

GUI at full 200 A load / 5 phases:



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PMP-10393 600 mV 120/200A 5-6 phases off 12Vin Test Report (TPS53661 / CSD95372B)
Texas Instruments

Efficiency data on Model t12:

Vin in Volts	Iin Amperes	Vout	Iout	Efficiency %	Losses in W
11.999	12.070	0.5995	200.04	82.80	24.90
11.999	11.720	0.5995	195.03	83.14	23.71
11.999	11.373	0.5995	190.02	83.48	22.54
11.999	11.028	0.5995	185.01	83.82	21.41
11.999	10.686	0.5995	180.00	84.16	20.31
11.999	10.349	0.5995	174.99	84.49	19.26
11.999	10.016	0.5995	169.97	84.80	18.27
11.999	9.685	0.5996	164.96	85.11	17.30
11.999	9.357	0.5996	159.95	85.41	16.38
11.999	9.032	0.5996	154.93	85.71	15.48
11.999	8.709	0.5996	149.93	86.02	14.61
11.999	8.389	0.5996	144.92	86.32	13.77
11.999	8.073	0.5996	139.91	86.60	12.98
11.999	7.759	0.5996	134.91	86.88	12.21
11.999	7.447	0.5996	129.90	87.16	11.47
11.999	7.138	0.5996	124.90	87.43	10.76
11.999	6.832	0.5996	119.90	87.69	10.09
11.999	6.528	0.5996	114.90	87.95	9.44
11.999	6.227	0.5996	109.90	88.19	8.82
11.999	5.929	0.5996	104.91	88.42	8.24
11.999	5.636	0.5996	99.97	88.65	7.68
11.999	5.627	0.5996	99.83	88.65	7.66
11.999	5.334	0.5996	94.86	88.87	7.12
11.999	5.043	0.5996	89.89	89.07	6.62
11.999	4.754	0.5996	84.90	89.25	6.13
11.999	4.467	0.5997	79.91	89.39	5.68
11.999	4.183	0.5996	74.92	89.51	5.26
11.999	3.900	0.5997	69.93	89.60	4.87
11.999	3.620	0.5997	64.93	89.63	4.50
11.999	3.342	0.5997	59.93	89.62	4.16
11.999	3.066	0.5997	54.93	89.54	3.85
11.999	2.792	0.5997	49.93	89.37	3.56
11.999	2.527	0.5997	44.93	88.87	3.37
11.999	2.261	0.5997	39.93	88.28	3.18
11.999	1.985	0.5997	34.93	87.96	2.87
11.999	1.704	0.5997	29.93	87.79	2.50
11.999	1.431	0.5997	24.93	87.09	2.22
11.999	1.166	0.5998	19.94	85.48	2.03
11.999	0.908	0.5998	14.94	82.28	1.93
11.999	0.652	0.5998	9.94	76.17	1.86
11.999	0.399	0.5998	4.95	61.98	1.82
11.999	0.149	0.5998	0.00	0.00	1.79

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Question arose about using this design for cases when Vin / Vout is greater than about 13 to 1 and minimum pulse width of about 260 nsec effectively removes the active current sharing with each phase being driven with a fixed on time in turn.

What will happen if the FETs have a “worst case” imbalance and there is no active current sharing?

I came up with an experiment with 3 phases 120A load and middle U20 FET being CSD95373B with 25% more Rdson, but same 5mV/A sense: The two outer FETs U100 & U300 remain the same CSD95372B's that have been in the design.

Model was run with fan on the U100 side and in each case until thermal stabilization. Then the Vin, Iin, Vout, Iout and phase frequency was recorded. Then the Iout from each phase and Vref were recorded, and the currents for each phase calculated based upon 5mV per A gain of this current sense. Then the thermal image of the board was taken with Flir EX320 thermal camera (e = 0.94) and the max temperatures of the 3 FETs recorded. At 12Vin data was taken for both 1.0 Vout with fixed frequency operation and active current sharing, and at 600 mV with fixed pulse width and no active current sharing occurs. Then at 600mV (all runs with 120 A load) the input voltage was reduced in steps to 7 Vin, with the mode transitioning back to fixed frequency as Vin was reduced below 9 Vin.

Summary of data:

							losses
Mode	Sw Freq	Vin (V)	Iin (A)	Vout(V)	Iout(A)	eff %	W
fix freq	321 kHz	12.071	11.640	1.013	120.0	86.5	18.95
fix pulse	226 kHz	12.067	7.445	0.611	120.0	81.6	16.52
fix pulse	260 kHz	10.53	8.543	0.611	120.0	81.5	16.64
fix pulse	305 kHz	9.027	10.000	0.611	120.0	81.2	16.95
fix freq	318 kHz	8.009	11.340	0.611	120.0	80.7	17.50
fix freq	318 kHz	6.97	13.045	0.611	120.0	80.6	17.60

		U100	U200	U300	sum	U100	U200	U300
		sensed	sensed	sensed	sensed	max		
		current-	current-	current-	current-	max	deg	max
Vin (V)	Vout(V)	A	A	A	A	deg C	C	deg C
12.071	1.013	39.1	37.5	39.3	115.9	57.5	69.9	59.4
12.067	0.611	42.6	30.6	43.2	116.4	56.0	56.9	58.1
10.53	0.611	42.6	30.8	43.2	116.6	56.5	57.6	58.8
9.027	0.611	42.2	31.2	43.2	116.6	56.6	58.3	59.5
8.009	0.611	39.2	38.0	39.2	116.4	56.0	68.8	57.8
6.97	0.611	39.2	38.2	39.2	116.6	55.7	68.6	57.7

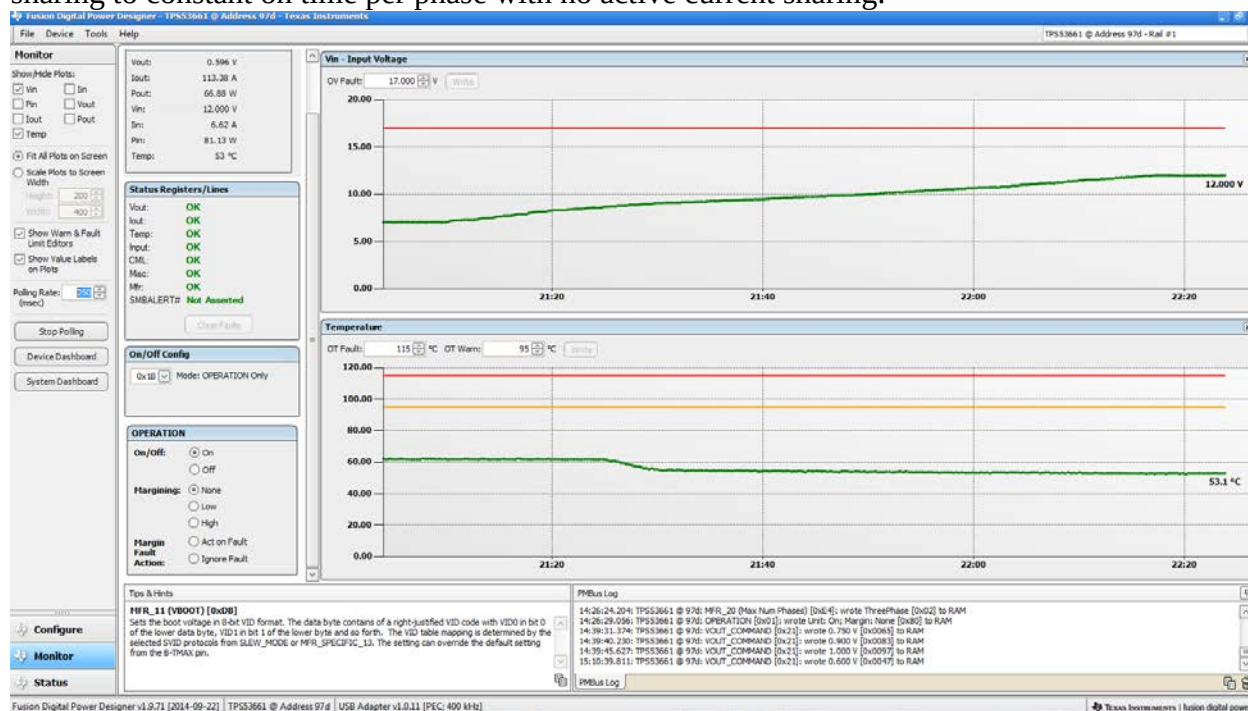
See actual thermal images below spread over 3 pages.

Conclusion: Allowing reduced frequency and fixed pulse widths can reduce temperature of hottest FET by as much as 10 degrees Celsius. This supported by both the Flir EX320 thermal camera and the internal temperature monitoring in the CSD9537xBs and TPS53661. (See next page for GUI.) In all previous high current 12V to low Vout / high current designs it has been assumed that increasing Vin makes efficiency worse. Here with mode transition and reduced frequency, efficiency is actually 1% better at 12 Vin than at 7 Vin.

PMP-10393 600 mV 120/200A 5-6 phases off 12Vin Test Report (TPS53661 / CSD95372B) Texas Instruments

GUI of temperature of hottest FET vs. Vin with 611mV 120A out:

In top image Vin is slowly increased from 7V to 12V: 8.7 degrees C reduction seen with most of change when Vin increased from 8V to 9V changing from constant frequency with active current sharing to constant on time per phase with no active current sharing:



In this image Vin is slowly reduced from 12V to 7V:

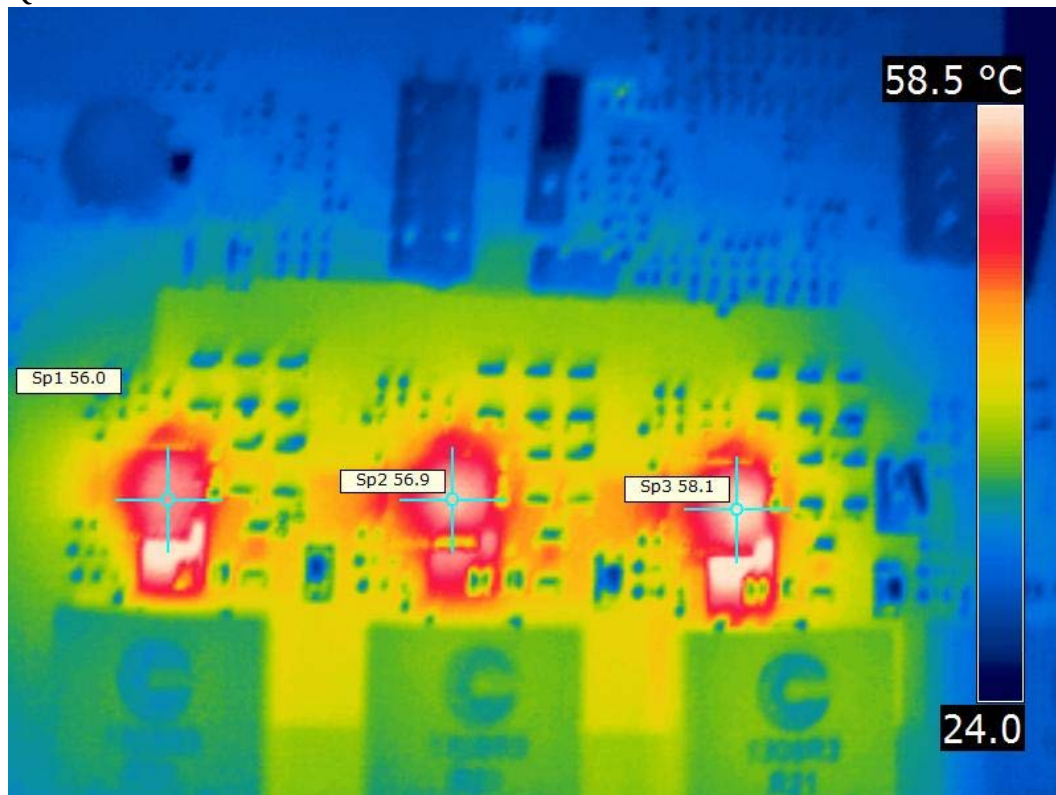


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Thermal Images for 3 phase experiment with U200 CSD95373B:12Vin 1.013V 120A out



Q 12Vin 611mV 120A out



Thermal Images for 3 phase experiment with U200 CSD95373B (cont.) 10.53 Vin 611mV 120A



9 Vin 611mV 120A out



Thermal Images for 3 phase experiment with U200 CSD95373B (cont.) 8 Vin 611mV 120A out



7 Vin 611mV 120A out



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